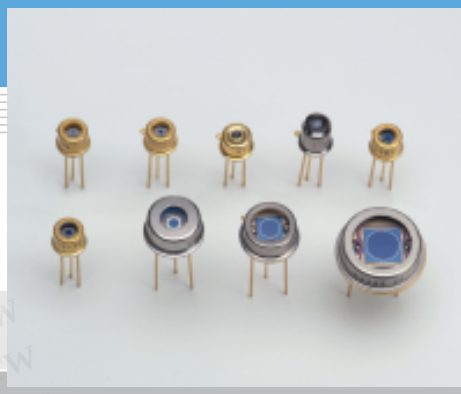


Si APD

S2381 to S2385, S5139, S8611, S3884

Low bias operation, for 800 nm band



Features

- Stable operation at low bias
- High-speed response
- High sensitivity and low noise

Applications

- Spatial light transmission
- Rangefinder

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 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
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General ratings / Absolute maximum ratings

Type No.	Dimensional outline/ Window material *1	Package	Active area *2 size (mm)	Effective active area (mm ²)	Absolute maximum ratings		
					Operating temperature Topr (°C)	Storage temperature Tstg (°C)	
S2381	①/K	TO-18	φ0.2	0.03	-20 to +85	-55 to +125	
S2382			φ0.5	0.19			
S5139							
S8611			φ1.0	0.78			
S2383	①/K	TO-5	φ1.5	1.77			
S2383-10 *3			φ3.0	7.0			
S3884			φ5.0	19.6			
S2384							
S2385	⑥/K	TO-8					

Electrical and optical characteristics (Typ. T_a=25 °C, unless otherwise noted)

Type No.	Spectral response range λ (nm)	Peak *4 sensitivity wavelength λ _p (nm)	Photo sensitivity S M=1 λ=800 nm (A/W)	Quantum efficiency QE M=1 λ=800 nm (%)	Breakdown voltage V _{BR} I _D =100 μA		Temp. coefficient of V _{BR} (V/°C)	Dark current *4 I _D		Cut-off *4 frequency f _c R _L =50 Ω (MHz)	Terminal *4 capacitance C _t (pF)	Excess Noise figure *4 x λ=800 nm	Gain M λ=800 nm
					Typ. (V)	Max. (V)		Typ. (nA)	Max. (nA)				
S2381	400 to 1000	800	0.5	75	150	200	0.65	0.05	0.5	1000	1.5	0.3	100
S2382								0.1	1	900	3		
S5139								0.2	2	600	6		
S8611								0.5	5	400	10		
S2383								1	10	120	40		
S2383-10 *3								3	30	40	95		
S3884												60	40
S2384													
S2385													

*1: Window material K: borosilicate glass, L: lens type borosilicate glass

*2: Active area in which a typical gain can be obtained

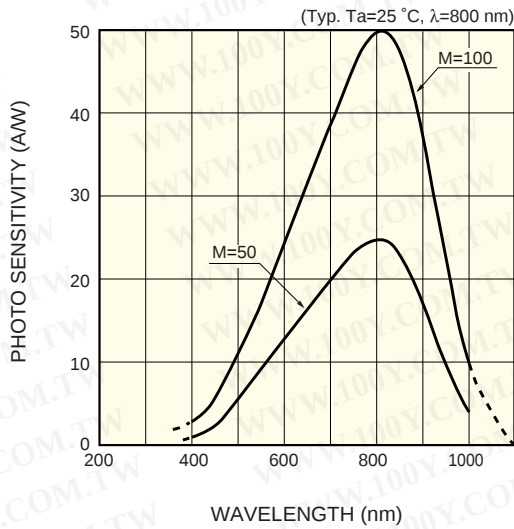
*3: This is a variant of S2383 in which the device chip is light-shielded by aluminum coating except for the active area

*4: Measured under conditions that the device is operated at the gain listed in the specification table

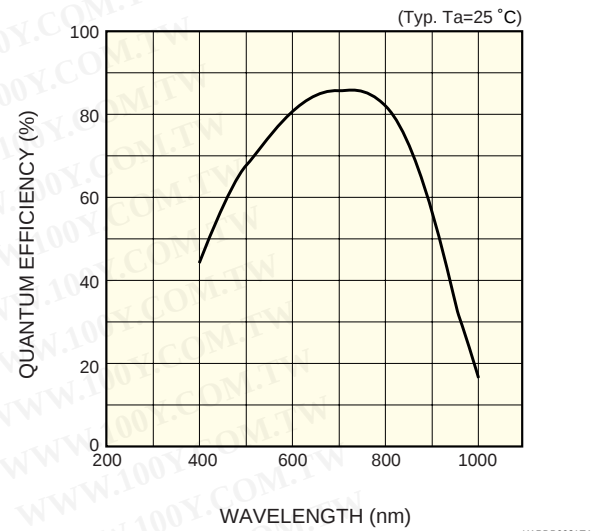
Note) The following 3 different breakdown voltage ranges are available for S2381, S2382, S5139, S8611, S2383/-10 and S3884.
 80 to 120 V, 120 to 160 V, 160 to 200 V

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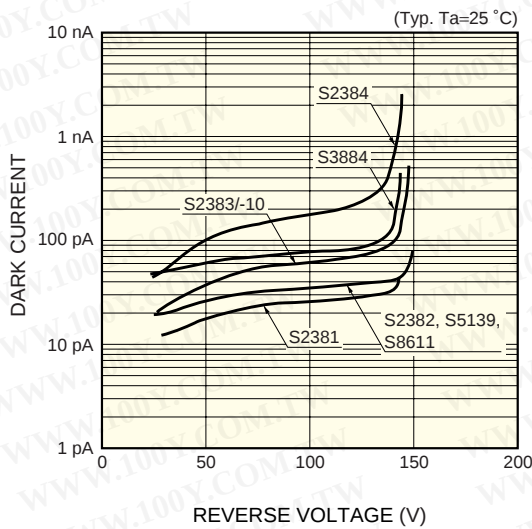
■ Spectral response



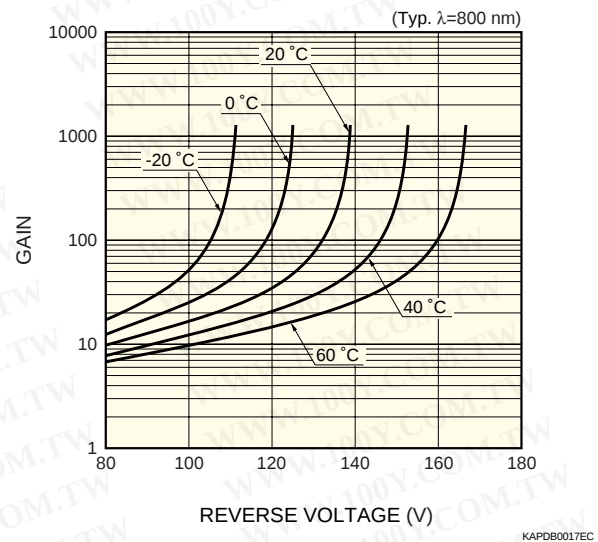
■ Quantum efficiency vs. wavelength



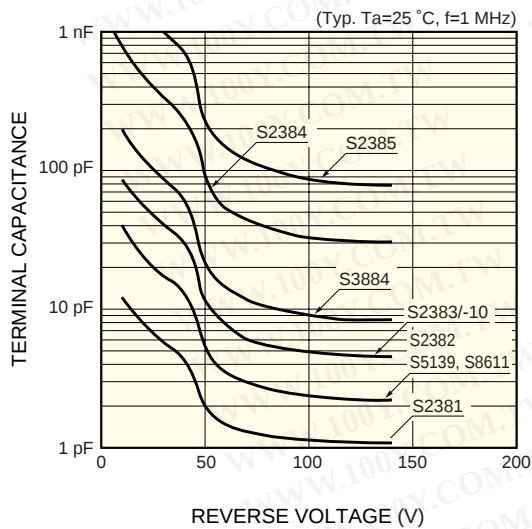
■ Dark current vs. reverse voltage



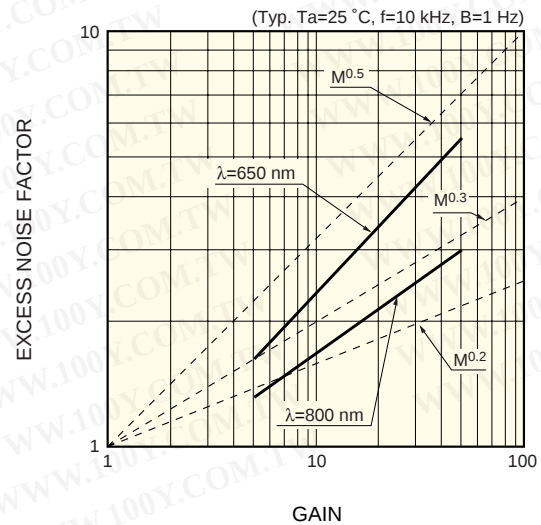
■ Gain vs. reverse voltage



■ Terminal capacitance vs. reverse voltage



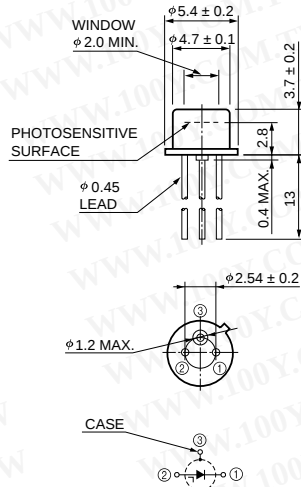
■ Excess noise factor vs. gain



Si APD S2381 to S2385, S5139, S8611, S3884

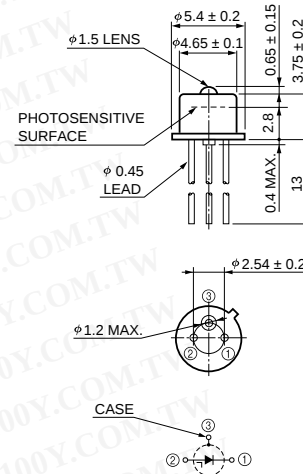
■ Dimensional outlines (unit: mm)

① S2381, S2382, S2383/-10



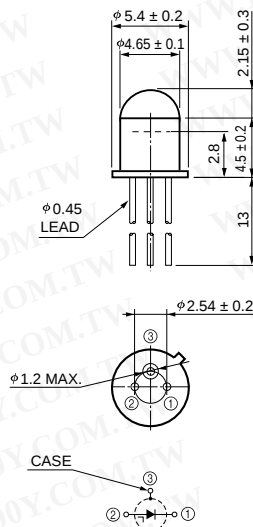
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② S5139



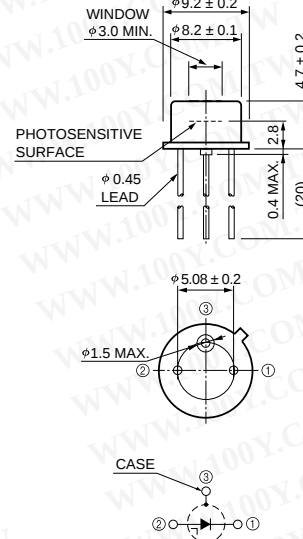
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③ S8611



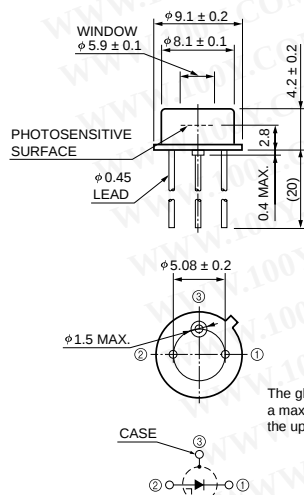
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④ S3884



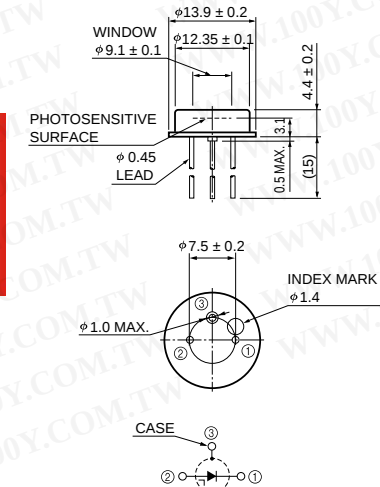
KAPDA0011EA

⑤ S2384



KAPDA0012EA

⑥ S2385



KAPDA0013EB

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The glass window may extend a maximum of 0.2 mm beyond the upper surface of the cap.

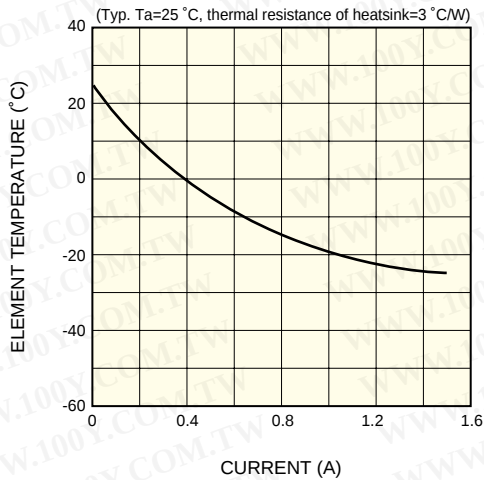
TE-cooled type APD S4315 series

Parameter	Symbol	Condition	S4315	S4315-01	S4315-02	Unit
APD	-		S2381	S2382	S2383	-
Effective active area *5	-		φ0.2	φ0.5	φ1.0	mm
Spectral response range	λ		400 to 1000			nm
Peak sensitivity wavelength	λ_p	M=100	800			nm
Cooling temperature	ΔT		35			°C
Package	-		TO-8			-

*5: Active area in which a typical gain can be obtained.

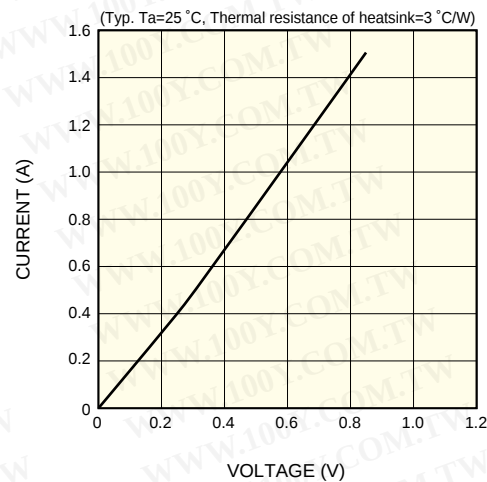
We welcome your request for active areas different from those listed above.

Cooling characteristic of TE-cooler



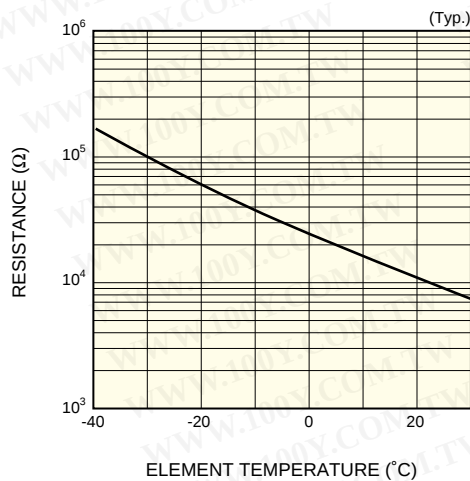
KAPDB0098EA

Current vs. voltage characteristic of TE-cooler



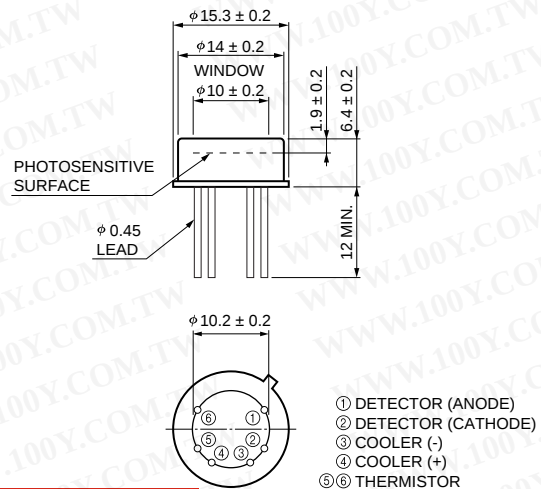
KAPDB0100EA

Thermistor temperature characteristic



KIRD0116EA

Dimensional outline (unit: mm)



KAPDA0020EA

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HAMAMATSU

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